

BSH111

N-channel enhancement mode field-effect transistor

Rev. 02 — 26 April 2002

Product data

1. Description

N-channel enhancement mode field-effect transistor in a plastic package using TrenchMOS™ technology.

Product availability:

BSH111 in SOT23.

2. Features

- TrenchMOS™ technology
- Very fast switching
- Low threshold voltage
- Subminiature surface mount package.

3. Applications

- Battery management
- High speed switch
- Logic level translator.

4. Pinning information

Table 1: Pinning - SOT23, simplified outline and symbol

Pin	Description	Simplified outline	Symbol
1	gate (g)	<p>Top view MSB003</p> <p>SOT23</p>	<p>MBB076</p>
2	source (s)		
3	drain (d)		

5. Quick reference data

Table 2: Quick reference data

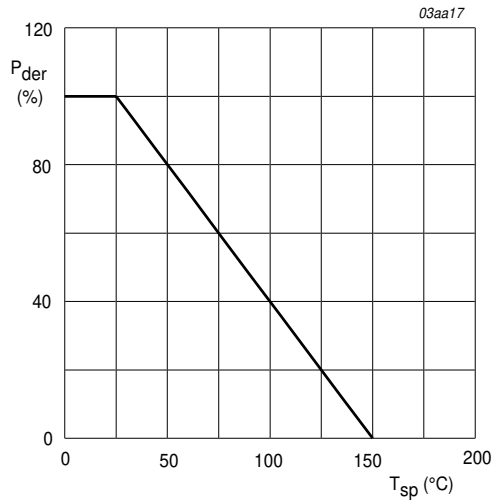
Symbol	Parameter	Conditions	Typ	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	55	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 4.5\text{ V}$	-	335	mA
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C}$	-	0.83	W
T_j	junction temperature		-	150	°C
$R_{DS(on)}$	drain-source on-state resistance	$V_{GS} = 4.5\text{ V}; I_D = 500\text{ mA}$	2.3	4.0	Ω
		$V_{GS} = 2.5\text{ V}; I_D = 75\text{ mA}$	2.4	5.0	Ω
		$V_{GS} = 1.8\text{ V}; I_D = 75\text{ mA}$	3.1	8.0	Ω

6. Limiting values

Table 3: Limiting values

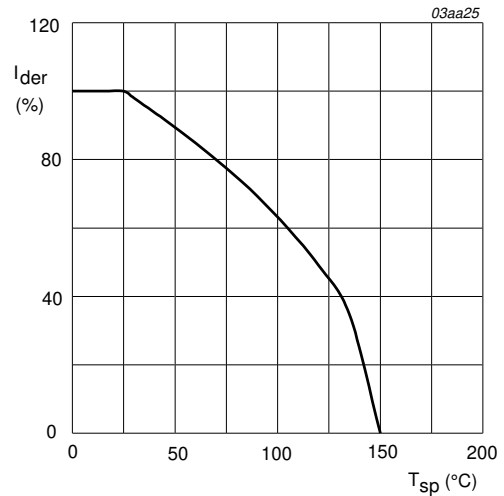
In accordance with the Absolute Maximum Rating System (IEC 60134).

Symbol	Parameter	Conditions	Min	Max	Unit
V_{DS}	drain-source voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}$	-	55	V
V_{DGR}	drain-gate voltage (DC)	$25\text{ °C} \leq T_j \leq 150\text{ °C}; R_{GS} = 20\text{ k}\Omega$	-	55	V
V_{GS}	gate-source voltage		-	± 10	V
I_D	drain current (DC)	$T_{sp} = 25\text{ °C}; V_{GS} = 4.5\text{ V};$ Figure 2 and 3	-	335	mA
		$T_{sp} = 100\text{ °C}; V_{GS} = 4.5\text{ V};$ Figure 2	-	212	mA
I_{DM}	peak drain current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s};$ Figure 3	-	1.3	A
P_{tot}	total power dissipation	$T_{sp} = 25\text{ °C};$ Figure 1	-	0.83	W
T_{stg}	storage temperature		-65	+150	°C
T_j	junction temperature		-65	+150	°C
Source-drain diode					
I_S	source (diode forward) current (DC)	$T_{sp} = 25\text{ °C}$	-	335	mA
I_{SM}	peak source (diode forward) current	$T_{sp} = 25\text{ °C};$ pulsed; $t_p \leq 10\text{ }\mu\text{s}$	-	1.3	A



$$P_{der} = \frac{P_{tot}}{P_{tot(25^{\circ}C)}} \times 100\%$$

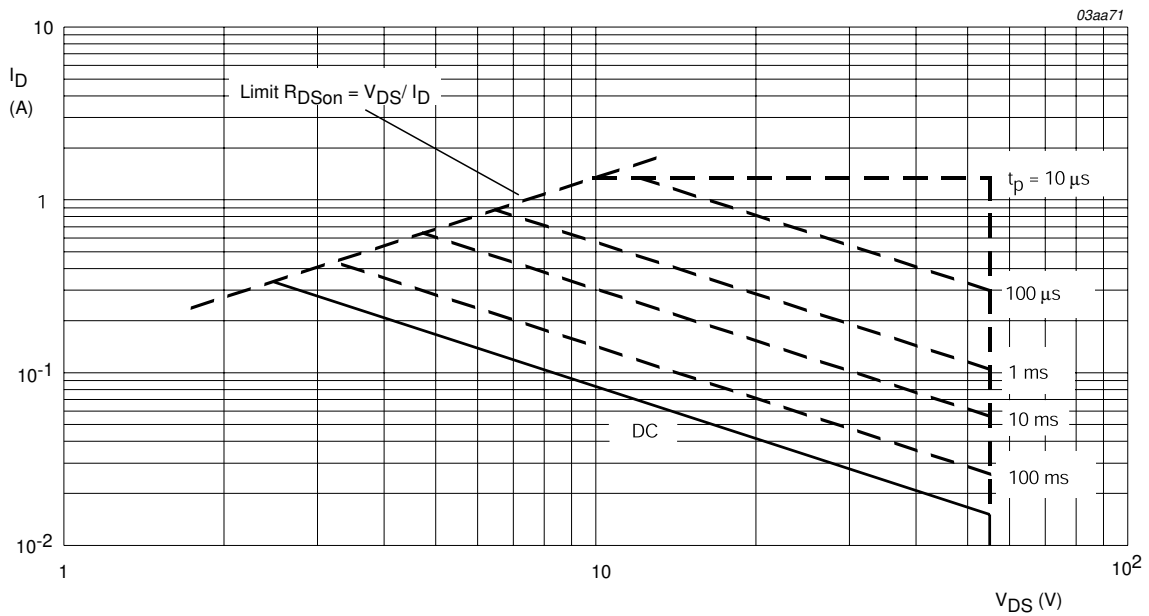
Fig 1. Normalized total power dissipation as a function of solder point temperature.



$$V_{GS} \geq 4.5 \text{ V}$$

$$I_{der} = \frac{I_D}{I_{D(25^{\circ}C)}} \times 100\%$$

Fig 2. Normalized continuous drain current as a function of solder point temperature.



T_{sp} = 25 °C; I_{DM} is single pulse.

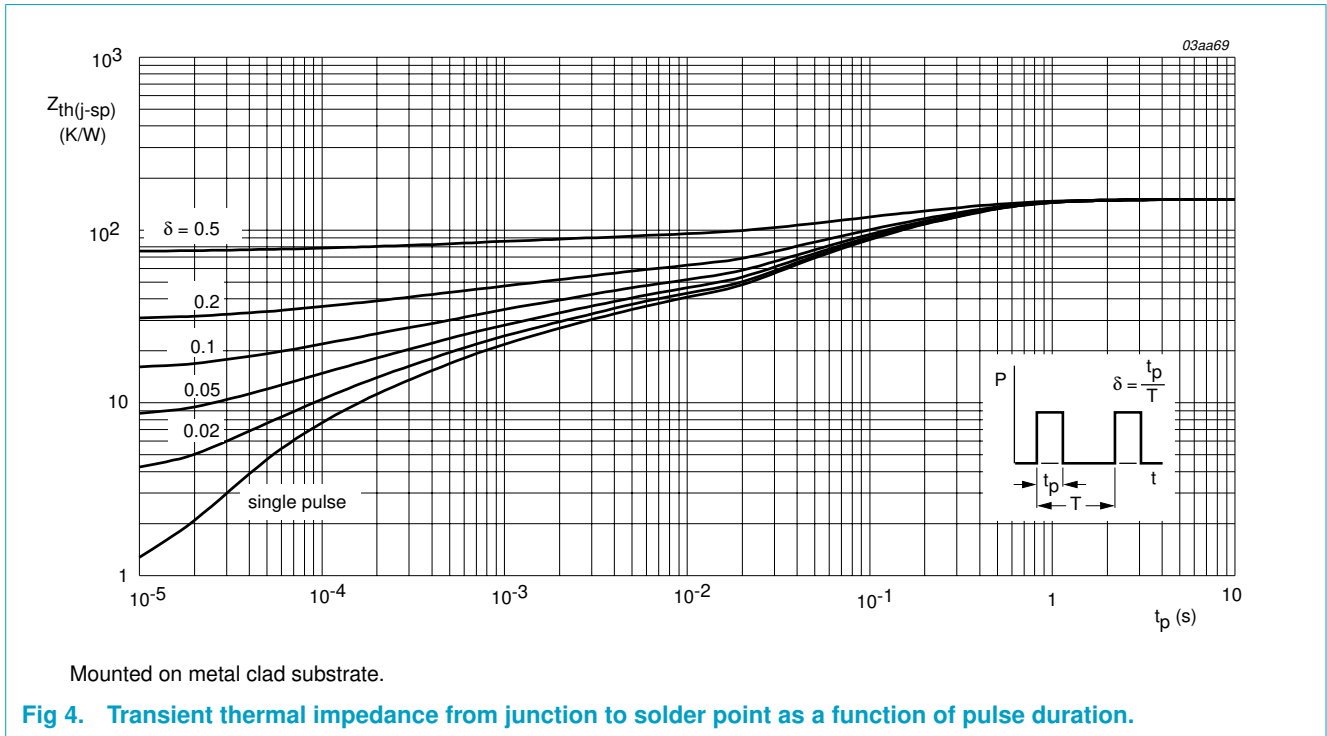
Fig 3. Safe operating area; continuous and peak drain currents as a function of drain-source voltage.

7. Thermal characteristics

Table 4: Thermal characteristics

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
$R_{th(j-sp)}$	thermal resistance from junction to solder point	mounted on metal clad substrate; Figure 4	-	-	150	K/W
$R_{th(j-a)}$	thermal resistance from junction to ambient	minimum footprint; mounted on printed circuit board	-	350	-	K/W

7.1 Transient thermal impedance



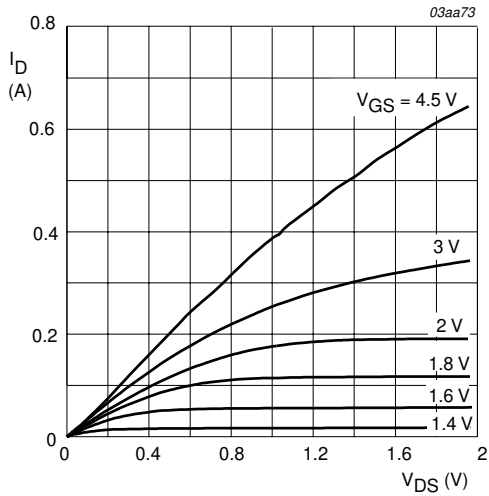
8. Characteristics

Table 5: Characteristics
T_j = 25 °C unless otherwise specified

Symbol	Parameter	Conditions	Min	Typ	Max	Unit	
Static characteristics							
V _{(BR)DSS}	drain-source breakdown voltage	I _D = 10 μA; V _{GS} = 0 V					
		T _j = 25 °C	55	75	-	V	
		T _j = -55 °C	50	-	-	V	
V _{GS(th)}	gate-source threshold voltage	I _D = 1 mA; V _{DS} = V _{GS} ; Figure 9					
		T _j = 25 °C	0.4	1.0	1.3	V	
		T _j = 150 °C	0.3	-	-	V	
		T _j = -55 °C	-	-	2.5	V	
I _{DSS}	drain-source leakage current	V _{DS} = 44 V; V _{GS} = 0 V					
		T _j = 25 °C	-	0.01	1.0	μA	
		T _j = 150 °C	-	-	10	μA	
I _{GSS}	gate-source leakage current	V _{GS} = ±8 V; V _{DS} = 0 V	-	10	100	nA	
R _{DS(on)}	drain-source on-state resistance	V _{GS} = 2.5 V; I _D = 75 mA; Figure 7 and 8					
		T _j = 25 °C	-	2.4	5	Ω	
		T _j = 150 °C	-	-	7.4	Ω	
		V _{GS} = 4.5 V; I _D = 500 mA; Figure 7 and 8					
		T _j = 25 °C	-	2.3	4	Ω	
		V _{GS} = 1.8 V; I _D = 75 mA; Figure 7 and 8					
T _j = 25 °C	-	3.1	8	Ω			
Dynamic characteristics							
g _{fs}	forward transconductance	V _{DS} = 10 V; I _D = 200 mA; Figure 11	100	380	-	mS	
Q _{g(tot)}	total gate charge	I _D = 0.5 A; V _{DS} = 44 V;	-	1.0	-	nC	
Q _{gs}	gate-source charge	V _{GS} = 8 V; Figure 14	-	0.05	-	nC	
Q _{gd}	gate-drain (Miller) charge		-	0.5	-	nC	
C _{iSS}	input capacitance	V _{GS} = 0 V; V _{DS} = 10 V;	-	17	40	pF	
C _{oss}	output capacitance	f = 1 MHz; Figure 12	-	7	30	pF	
C _{rSS}	reverse transfer capacitance		-	4	10	pF	
t _{on}	turn-on time	V _{DD} = 50 V; R _D = 250 Ω;	-	4	10	ns	
t _{off}	turn-off time	V _{GS} = 10 V; R _G = 50 Ω; R _{GS} = 50 Ω	-	11	15	ns	

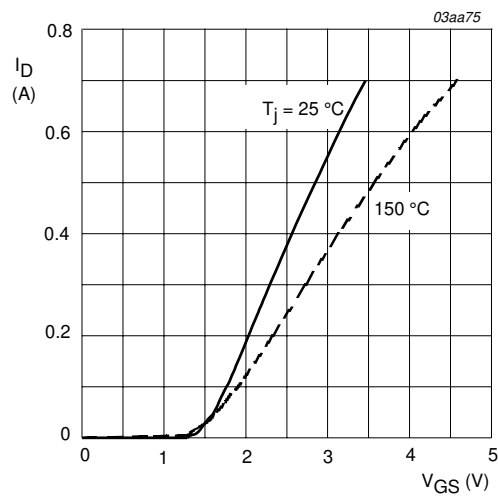
Table 5: Characteristics...continued*T_j = 25 °C unless otherwise specified*

Symbol	Parameter	Conditions	Min	Typ	Max	Unit
Source-drain diode						
V _{SD}	source-drain (diode forward) voltage	I _S = 300 mA; V _{GS} = 0 V; Figure 13	-	0.95	1.5	V
t _{rr}	reverse recovery time	I _S = 300 mA;	-	30	-	ns
Q _r	recovered charge	dI _S /dt = -100 A/μs; V _{GS} = 0 V; V _{DS} = 25 V	-	30	-	nC



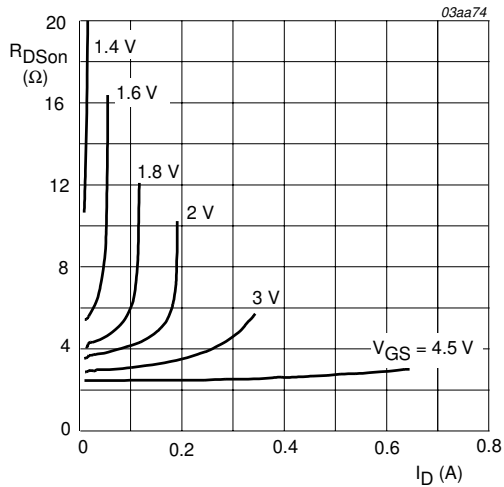
$T_j = 25\text{ }^\circ\text{C}$

Fig 5. Output characteristics: drain current as a function of drain-source voltage; typical values.



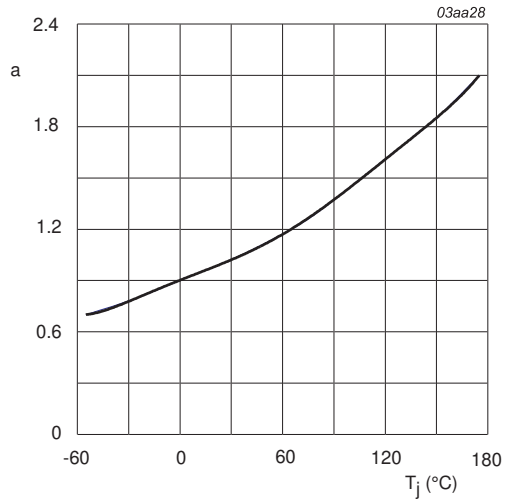
$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{DS} > I_D \times R_{DSon}$

Fig 6. Transfer characteristics: drain current as a function of gate-source voltage; typical values.



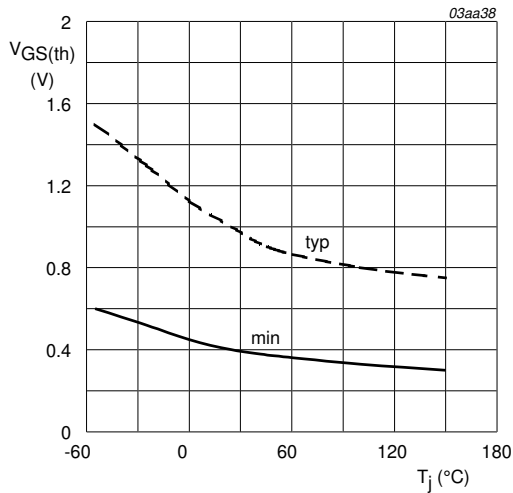
$T_j = 25\text{ }^\circ\text{C}$

Fig 7. Drain-source on-state resistance as a function of drain current; typical values.



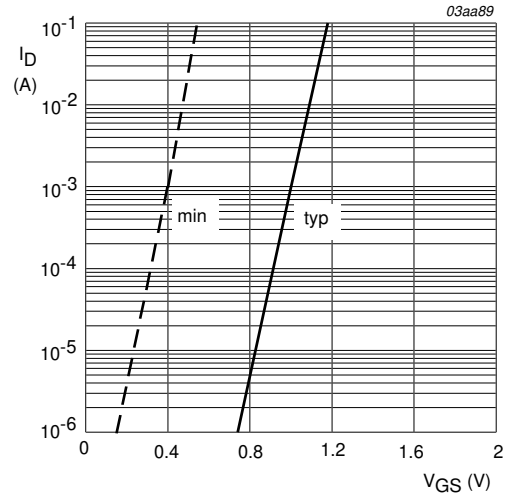
$$a = \frac{R_{DSon}}{R_{DSon(25^\circ\text{C})}}$$

Fig 8. Normalized drain-source on-state resistance factor as a function of junction temperature.



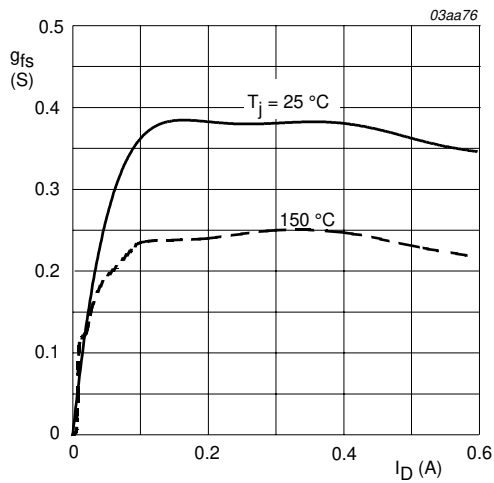
$I_D = 1 \text{ mA}; V_{DS} = V_{GS}$

Fig 9. Gate-source threshold voltage as a function of junction temperature.



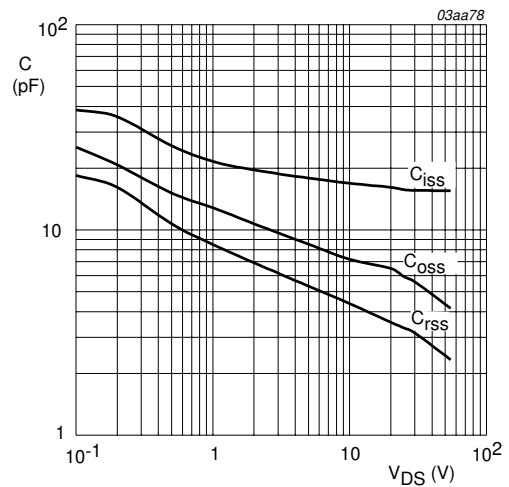
$T_J = 25 \text{ }^\circ\text{C}; V_{DS} = 5 \text{ V}$

Fig 10. Sub-threshold drain current as a function of gate-source voltage.



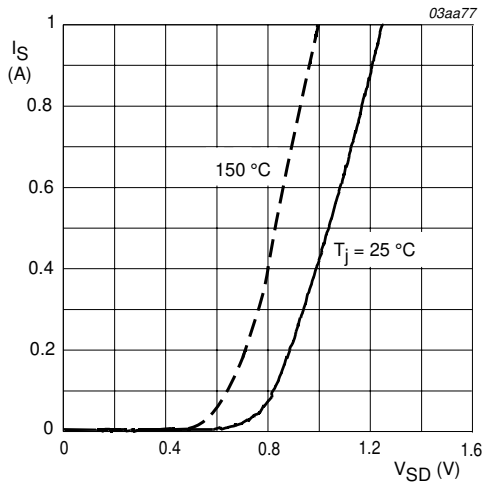
$T_J = 25 \text{ }^\circ\text{C and } 150 \text{ }^\circ\text{C}; V_{DS} > I_D \times R_{DS(on)}$

Fig 11. Forward transconductance as a function of drain current; typical values.



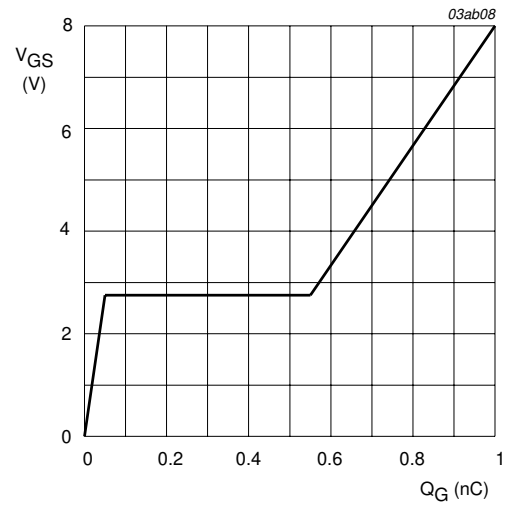
$V_{GS} = 0 \text{ V}; f = 1 \text{ MHz}$

Fig 12. Input, output and reverse transfer capacitances as a function of drain-source voltage; typical values.



$T_j = 25\text{ }^\circ\text{C}$ and $150\text{ }^\circ\text{C}$; $V_{GS} = 0\text{ V}$

Fig 13. Source (diode forward) current as a function of source-drain (diode forward) voltage; typical values.



$I_D = 0.5\text{ A}$; $V_{DS} = 44\text{ V}$

Fig 14. Gate-source voltage as a function of gate charge; typical values.

9. Package outline

Plastic surface mounted package; 3 leads

SOT23

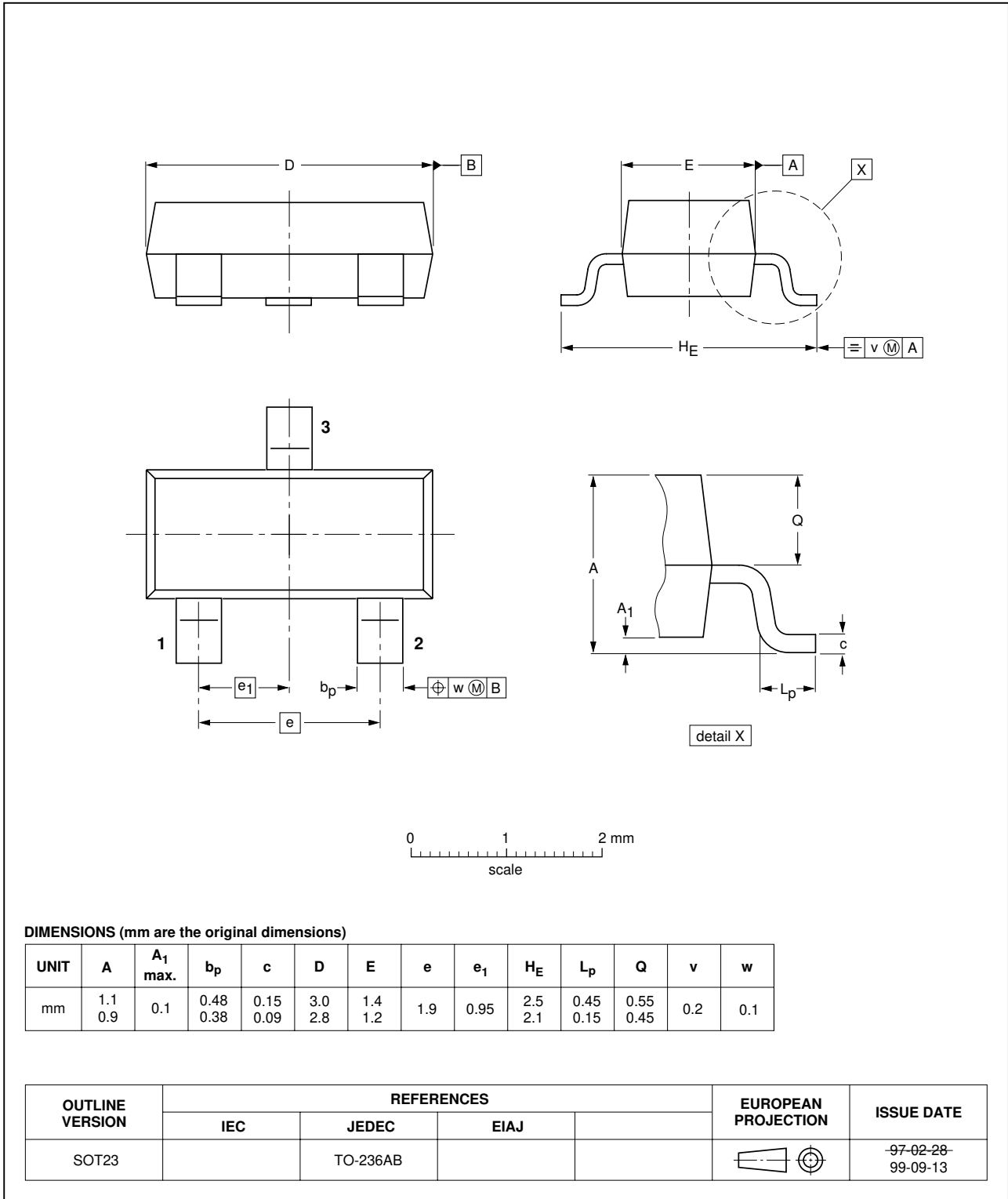


Fig 15. SOT23.

10. Revision history

Table 6: Revision history

Rev	Date	CPCN	Description
02	20020426	-	Product data (9397 750 09629) Modifications <ul style="list-style-type: none">• V_{GS} data updated.
01	20000807	-	Product specification; initial version.

11. Data sheet status

Data sheet status ^[1]	Product status ^[2]	Definition
Objective data	Development	This data sheet contains data from the objective specification for product development. Philips Semiconductors reserves the right to change the specification in any manner without notice.
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[2] The product status of the device(s) described in this data sheet may have changed since this data sheet was published. The latest information is available on the Internet at URL <http://www.semiconductors.philips.com>.

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Limiting values definition — Limiting values given are in accordance with the Absolute Maximum Rating System (IEC 60134). Stress above one or more of the limiting values may cause permanent damage to the device. These are stress ratings only and operation of the device at these or at any other conditions above those given in the Characteristics sections of the specification is not implied. Exposure to limiting values for extended periods may affect device reliability.

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